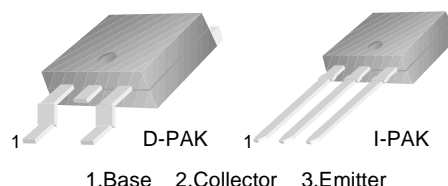


MJD32/32C

MJD32/32C

General Purpose Amplifier Low Speed Switching Applications D-PAK for Surface Mount Applications

- Load Formed for Surface Mount Application (No Suffix)
- Straight Lead (I-PAK, "- I" Suffix)
- Electrically Similar to Popular TIP32 and TIP32C



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | - 40 | V |
| | : MJD32 : MJD32C | - 100 | V |
| V_{CEO} | Collector-Emitter Voltage | - 40 | V |
| | : MJD32 : MJD32C | - 100 | V |
| V_{EBO} | Emitter-Base Voltage | - 5 | V |
| I_C | Collector Current (DC) | - 3 | A |
| I_{CP} | Collector Current (Pulse) | - 5 | A |
| I_B | Base Current | - 1 | A |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 15 | W |
| | Collector Dissipation ($T_a=25^\circ\text{C}$) | 1.56 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 65 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|----------------|--|--|----------|------|---------------|
| $V_{CEO(sus)}$ | * Collector-Emitter Sustaining Voltage | $I_C = - 30\text{mA}$, $I_B = 0$ | -40 | | V |
| | : MJD32 : MJD32C | | | | V |
| I_{CEO} | Collector Cut-off Current | $V_{CE} = - 40\text{V}$, $I_B = 0$ $V_{CE} = - 60\text{V}$, $I_B = 0$ | | -50 | μA |
| | : MJD32 : MJD32C | | | | μA |
| I_{CES} | Collector Cut-off Current | $V_{CE} = - 40\text{V}$, $V_{BE} = 0$ $V_{CE} = - 100\text{V}$, $V_{BE} = 0$ | | -20 | μA |
| | : MJD32 : MJD32C | | | | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{BE} = - 5\text{V}$, $I_C = 0$ | | -1 | mA |
| h_{FE} | * DC Current Gain | $V_{CE} = - 4\text{V}$, $I_C = - 1\text{A}$ $V_{CE} = - 4\text{V}$, $I_C = - 3\text{A}$ | 25 10 | 50 | |
| $V_{CE(sat)}$ | * Collector-Emitter Saturation Voltage | $I_C = - 3$, $I_B = - 375\text{mA}$ | | -1.2 | V |
| $V_{BE(on)}$ | * Base-Emitter ON Voltage | $V_{CE} = - 4\text{A}$, $I_C = - 3\text{A}$ | | -1.8 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = - 10\text{V}$, $I_C = - 500\text{mA}$ | 3 | | MHz |

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

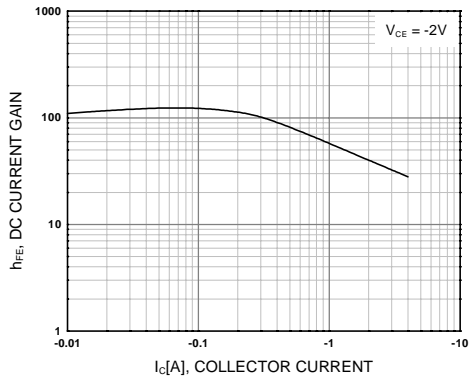


Figure 1. DC current Gain

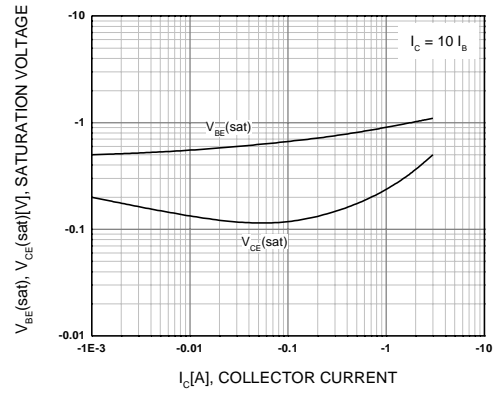


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

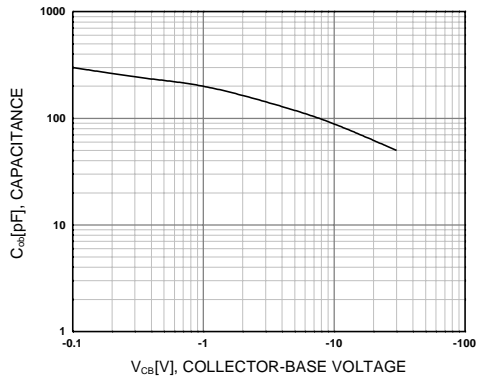


Figure 3. Collector Capacitance

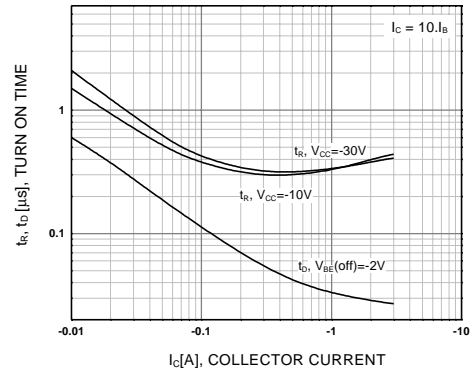


Figure 4. Turn On Time

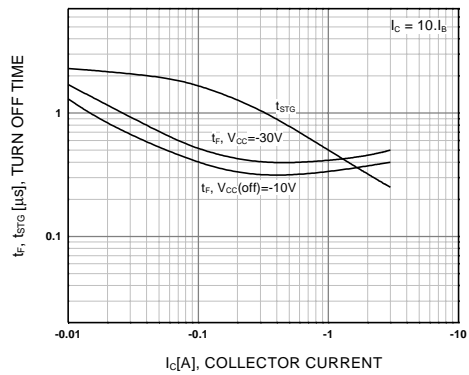


Figure 5. Turn Off Time

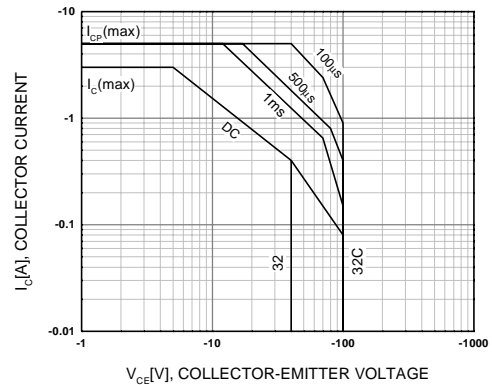


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

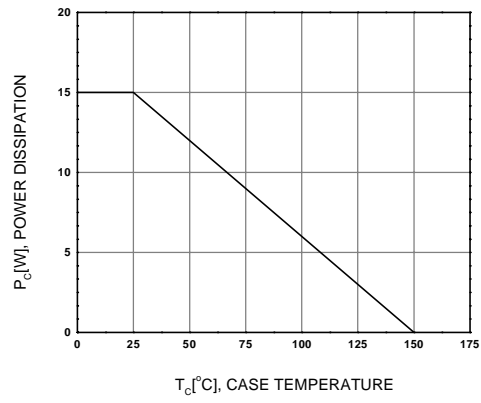
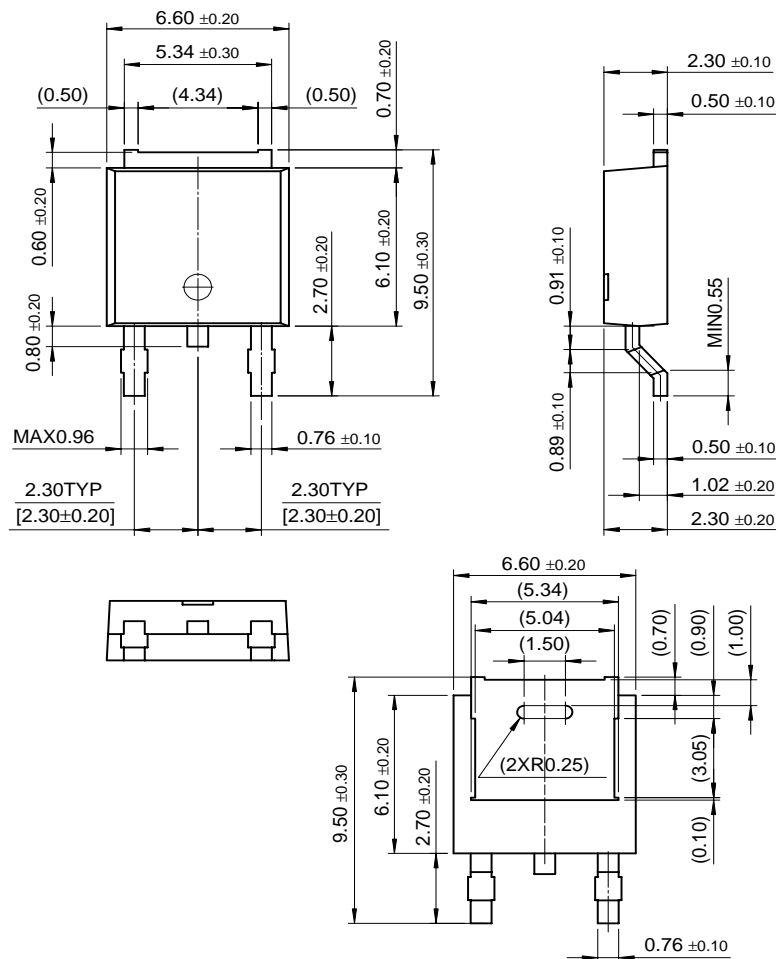


Figure 7. Power Derating

D-PAK



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